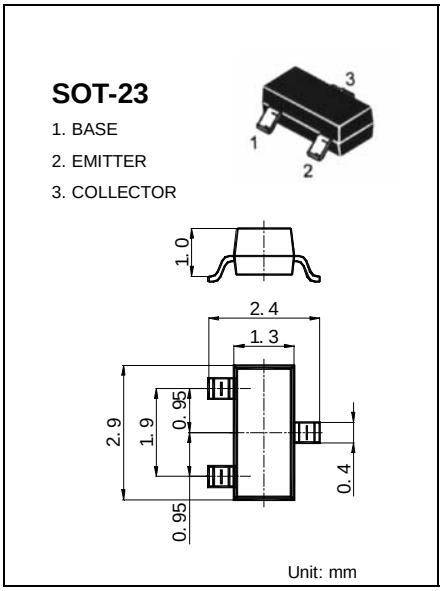
Shenzhen Tuofeng Semiconductor Technology Co., Ltd

SOT-23 Plastic-Encapsulate Transistors

SS8050LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 0.3 W (Tamb=25℃)

Collector current

$I_{CM:}$ 1.2 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 0.1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CB}=20V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C= 100mA	120		350	
	$h_{FE(2)}$	V_{CE}=1V, I_C= 800mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=800mA, I_B= 80mA			0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=800mA, I_B= 80mA			1.2	V
Transition frequency	f_T	V_{CE}=6V, I_C= 20mA f=30MHz	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	120-200	200-350

DEVICE MARKING	**SS8050LT1=Y1**

Typical Characteristics

